# **General Description**

The MAX1748 triple-output DC-DC converter in a lowprofile TSSOP package provides the regulated voltages required by active matrix, thin-film transistor (TFT) liquid crystal displays (LCDs). One high-power DC-DC converter and two low-power charge pumps convert the +3.3V to +5V input supply voltage into three independent output voltages.

The primary high-power DC-DC converter generates a boosted output voltage (V<sub>MAIN</sub>) up to 13V that is regulated within ±1%. The low-power BiCMOS control circuitry and the low on-resistance ( $0.35\Omega$ ) of the integrated power MOSFET allows efficiency up to 93%. The 1MHz current-mode PWM architecture provides fast transient response and allows the use of ultra-small inductors and ceramic capacitors.

The dual charge pumps independently regulate one positive output (VPOS) and one negative output (VNEG). These low-power outputs use external diode and capacitor stages (as many stages as required) to regulate output voltages up to +40V and down to -40V. A proprietary regulation algorithm minimizes output ripple, as well as capacitor sizes for both charge pumps.

The MAX1748 is available in the ultra-thin TSSOP package (1.1mm max height).

## **Features**

- Three Integrated DC-DC Converters
- 1MHz Current-Mode PWM Boost Regulator Up to +13V Main High-Power Output ±1% Accuracy High Efficiency (93%)
- Dual Charge-Pump Outputs
   Up to +40V Positive Charge-Pump Output
   Down to -40V Negative Charge-Pump Output
- Internal Supply Sequencing
- Internal Power MOSFETs
- +2.7V to +5.5V Input Supply
- 0.1µA Shutdown Current
- 0.6mA Quiescent Current
- Internal Soft-Start
- Power-Ready Output
- Ultra-Small External Components
- Thin TSSOP Package (1.1mm max)

## **Ordering Information**

PART	TEMP. RANGE	PIN-PACKAGE
MAX1748EUE	-40°C to +85°C	16 TSSOP

## \_\_\_Applications

TFT Active Matrix LCD Displays Passive Matrix LCD Displays PDAs Digital Still Cameras Camcorders

Typical Operating Circuit appears at end of data sheet.



13 SUPP

12 DRVP

11 SUPN

10 DRVN

9 SHDN

IN 4 MAX1748 GND 5 REF 6 FBP 7 FBN 8 TSSOP

TOP VIEW

## M/IXI/M

\_ Maxim Integrated Products 1

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## **ABSOLUTE MAXIMUM RATINGS**

IN, SHDN, TGND to GND DRVN to GND		Continuous Power Dissipation (T <sub>A</sub> = + 16-Pin TSSOP (derate 9.4mW/°C abo	
DRVP to GND	0.3V to (V <sub>SUPP</sub> + 0.3V)	Operating Temperature Range	
PGND to GND	±0.3V	MAX1748EUE	40°C to +85°C
RDY to GND	0.3V to +14V	Junction Temperature	
LX, SUPP, SUPN to PGND	0.3V to +14V	Storage Temperature Range	
INTG, REF, FB, FBN, FBP to GND	0.3V to (V <sub>IN</sub> + 0.3V)	Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **ELECTRICAL CHARACTERISTICS**

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = 10V, TGND = PGND = GND, C_{REF} = 0.22\mu$ F,  $C_{INTG} = 470$ pF, **T<sub>A</sub> = 0°C to +85°C**, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	МАХ	UNITS	
Input Supply Range	V <sub>IN</sub>		2.7		5.5	V	
Input Undervoltage Threshold	VUVLO	VIN rising, 40mV hysteresis (typ)	2.2	2.4	2.6	V	
IN Quiescent Supply Current	l <sub>IN</sub>	$V_{FB} = V_{FBP} = 1.5V, V_{FBN} = -0.2V$		0.6	1	mA	
SUPP Quiescent Current	ISUPP	V <sub>FBP</sub> = 1.5V		0.4	0.8	mA	
SUPN Quiescent Current	ISUPN	V <sub>FBN</sub> = -0.1V		0.4	0.8	mA	
IN Shutdown Current		$V\overline{SHDN} = 0, VIN = 5V$		0.1	10	μA	
SUPP Shutdown Current		$V\overline{SHDN} = 0, VSUPP = 13V$		0.1	10	μA	
SUPN Shutdown Current		$V\overline{SHDN} = 0, V_{SUPN} = 13V$		0.1	10	μA	
MAIN BOOST CONVERTER							
Output Voltage Range	VMAIN		VIN		13	V	
FB Regulation Voltage	VFB	$T_A = 0^{\circ}C \text{ to } +85^{\circ}C$	1.235	1.248	1.261	V	
FB Input Bias Current	I <sub>FB</sub>	V <sub>FB</sub> = 1.25V, INTG = GND	-50		50	nA	
Operating Frequency	fosc		0.85	1	1.15	MHz	
Oscillator Maximum Duty Cycle			78	85	90	%	
Load Regulation		$I_{MAIN} = 0$ to 200mA, $V_{MAIN} = 10V$		0.2		%	
Line Regulation				0.1		%/V	
Integrator Gm				320		μmho	
LX Switch On-Resistance	R <sub>LX(ON)</sub>	I <sub>LX</sub> = 100mA		0.35	0.7	Ω	
LX Leakage Current	ILX	$V_{LX} = 13V$		0.01	20	μA	
		Phase I = soft-start (1.0ms)	0.275	0.380	0.500		
LV Current Limit	1	Phase II = soft-start (1.0ms)		0.75			
LX Current Limit	ILX(MAX)	Phase III = soft-start (1.0ms)		1.12		A	
		Phase IV = fully on (after 3.0ms)	1.1	1.5	2.0		
Maximum RMS LX Current				1		А	
Soft-Start Period	t <sub>SS</sub>	Power-up to the end of Phase III		3072 / fosc		S	
FB Fault Trip Level			1.07	1.1	1.14	V	
POSITIVE CHARGE PUMP							
V <sub>SUPP</sub> Input Supply Range	VSUPP		2.7		13	V	



# **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = 10V, TGND = PGND = GND, C_{REF} = 0.22\mu$ F,  $C_{INTG} = 470$ pF,  $T_A = 0^{\circ}$ C to +85°C, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS	
Operating Frequency				0.5×		Hz	
Operating requency				fosc		1 IZ	
FBP Regulation Voltage	VFBP		1.20	1.25	1.30	V	
FBP Input Bias Current	IFBP	$V_{\text{FBP}} = 1.5 V$	-50		50	nA	
DRVP PCH On-Resistance				3	10	Ω	
DRVP NCH On-Resistance		V <sub>FBP</sub> = 1.213V		1.5	4	Ω	
DAVE NOT OIT-nesistance		V <sub>FBP</sub> = 1.275V	20			kΩ	
FBP Power-Ready Trip Level		Rising edge	1.091	1.125	1.159	V	
FBP Fault Trip Level		Falling edge		1.11		V	
Maximum RMS DRVP Current				0.1		А	
NEGATIVE CHARGE PUMP							
V <sub>SUPN</sub> Input Supply Range	VSUPN		2.7		13	V	
				0.5×			
Operating Frequency				fosc		Hz	
FBN Regulation Voltage	V <sub>FBN</sub>		-50	0	50	mV	
FBN Input Bias Current	IFBN	$V_{\text{FBN}} = -0.05 V$	-50		50	nA	
DRVN PCH On-Resistance				3	10	Ω	
DRVN NCH On-Resistance		$V_{\text{FBN}} = 0.035 \text{V}$		1.5	4	Ω	
DRVIN INCH OII-RESISTANCE		$V_{\text{FBN}} = -0.025 V$	20			kΩ	
FBN Power-Ready Trip Level		Rising edge	80	110	165	mV	
FBN Fault Trip Level		Falling edge		130		mV	
Maximum RMS DRVN Current				0.1		А	
REFERENCE			•				
Reference Voltage	VREF	-2μΑ < I <sub>REF</sub> < 50μΑ	1.231	1.25	1.269	V	
Reference Undervoltage		V <sub>REF</sub> rising	0.9	1.05	1.2	V	
Threshold		VREFTISTING	0.9	1.05	1.2	v	
LOGIC SIGNALS	1	1	r.			1	
SHDN Input Low Voltage		0.4V hysteresis (typ)			0.9	V	
SHDN Input High Voltage			2.1			V	
SHDN Input Current	I SHDN			0.01	1	μΑ	
RDY Output Low Voltage		I <sub>SINK</sub> = 2mA		0.25	0.5	V	
RDY Output High Voltage		$V_{\overline{RDY}} = 13V$		0.01	1	μA	

# **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = 10V, TGND = PGND = GND, C_{REF} = 0.22\mu$ F,  $C_{INTG} = 470$ pF,  $T_A = -40$ °C to +85°C, unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNITS
Input Supply Range	VIN		2.7	5.5	V
Input Undervoltage Threshold	Vuvlo	V <sub>IN</sub> rising, 40mV hysteresis (typ)	2.2	2.6	V
IN Quiescent Supply Current	I <sub>IN</sub>	$V_{FB} = V_{FBP} = 1.5V, V_{FBN} = -0.2V$		1	mA
SUPP Quiescent Current	ISUPP	V <sub>FBP</sub> = 1.5V		0.8	mA
SUPN Quiescent Current	ISUPN	V <sub>FBN</sub> = -0.1V		0.8	mA
IN Shutdown Current		$V_{\overline{SHDN}} = 0, V_{IN} = 5V$		10	μΑ
SUPP Shutdown Current		$V_{\overline{SHDN}} = 0, V_{SUPP} = 13V$		10	μΑ
SUPN Shutdown Current		$V_{\overline{SHDN}} = 0, V_{SUPN} = 13V$		10	μΑ
MAIN BOOST CONVERTER			·		
Output Voltage Range	VMAIN		VIN	13	V
FB Regulation Voltage	VFB		1.225	1.271	V
FB Input Bias Current	I <sub>FB</sub>	V <sub>FB</sub> = 1.25V, INTG = GND	-50	50	nA
Operating Frequency	Fosc		0.75	1.25	MHz
Oscillator Maximum Duty Cycle			78	90	%
LX Switch On-Resistance	R <sub>LX(ON)</sub>	I <sub>LX</sub> = 100mA		0.7	Ω
LX Leakage Current	ILX	V <sub>LX</sub> = 13V		20	μA
	I <sub>LX(MAX)</sub>	Phase I = soft-start (1.0ms)	0.275	0.500	A
LX Current Limit		Phase IV = fully on (after 3.0ms)	1.1	2.0	
FB Fault Trip Level			1.07	1.14	V
POSITIVE CHARGE PUMP			·		
SUPP Input Supply Range	VSUPP		2.7	13	V
FBP Regulation Voltage	VFBP		1.20	1.30	V
FBP Input Bias Current	IFBP	V <sub>FBP</sub> = 1.5V	-50	50	nA
DRVP PCH On-Resistance				10	Ω
		V <sub>FBP</sub> = 1.213V		4	Ω
DRVP NCH On-Resistance		V <sub>FBP</sub> = 1.275V	20		kΩ
FBP Power-Ready Trip Level		Rising edge	1.091	1.159	V
NEGATIVE CHARGE PUMP					
SUPN Input Supply Range	VSUPN		2.7	13	V
FBN Regulation Voltage	VFBN		-50	50	mV
FBN Input Bias Current	I <sub>FBN</sub>	V <sub>FBN</sub> = -0.05V	-50	50	nA
DRVN PCH On-Resistance				10	Ω
		V <sub>FBN</sub> = 0.035V		4	Ω
DRVN NCH On-Resistance		V <sub>FBN</sub> = -0.025V	20		kΩ
FBN Power-Ready Trip Level		Rising edge	80	165	mV
REFERENCE	•	·			
Reference Voltage	VREF	-2μΑ < I <sub>REF</sub> < 50μΑ	1.223	1.269	V
Reference Undervoltage		V <sub>REF</sub> rising	0.9	1.2	V

## **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = 10V, TGND = PGND = GND, C_{REF} = 0.22\mu$ F,  $C_{INTG} = 470$  pF,  $T_A = -40$ °C to +85°C, unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNITS		
LOGIC SIGNALS	LOGIC SIGNALS						
SHDN Input Low Voltage		0.45V hysteresis (typ)		0.9	V		
SHDN Input High Voltage			2.1		V		
SHDN Input Current	ISHDN			1	μΑ		
RDY Output Low Voltage		I <sub>SINK</sub> = 2mA		0.5	V		
RDY Output High Leakage		V <sub>RDY</sub> = 13V		1	μΑ		

Note 1: Specifications from 0°C to -40°C are guaranteed by design, not production tested.

(Circuit of Figure 5,  $V_{IN}$  = 3.3V,  $T_A$  = +25°C, unless otherwise noted.)



**Typical Operating Characteristics** 





## **Typical Operating Characteristics (continued)**

(Circuit of Figure 5,  $V_{IN}$  = 3.3V,  $T_A$  = +25°C, unless otherwise noted.)



## **Pin Description**

PIN	NAME	FUNCTION	
1	RDY	Active-Low Open-Drain Output. Indicates all outputs are ready. The on-resistance is 125 $\Omega$ (typ).	
2	FB	Main Boost Regulator Feedback Input. Regulates to 1.248V nominal. Connect feedback resistive divider to analog ground (GND).	
3	INTG	Main Boost Integrator Output. If used, connect 470pF to analog ground (GND). To disable integrator, connect to REF.	
4	IN	Supply Input. +2.7V to +5.5V input range. Bypass with a 0.1 $\mu$ F capacitor between IN and GND, as close to the pins as possible.	
5	GND	Analog Ground. Connect to power ground (PGND) underneath the IC.	
6	REF	Internal Reference Bypass Terminal. Connect a 0.22 $\mu$ F capacitor from this terminal to analog ground (GND). External load capability to 50 $\mu$ A.	
7	FBP	Positive Charge-Pump Regulator Feedback Input. Regulates to 1.25V nominal. Connect feedback resistive divider to analog ground (GND).	
8	FBN	Negative Charge-Pump Regulator Feedback Input. Regulates to 0V nominal.	
9	SHDN	Active-Low Logic-Level Shutdown Input. Connect SHDN to IN for normal operation.	
10	DRVN	Negative Charge-Pump Driver Output. Output high level is V <sub>SUPN</sub> , and low level is PGND.	
11	SUPN	Negative Charge-Pump Driver Supply Voltage. Bypass to PGND with a $0.1\mu F$ capacitor.	
12	DRVP	Positive Charge-Pump Driver Output. Output high level is V <sub>SUPP</sub> , and low level is PGND.	

## M/X/W

Pin Description (continu					
PIN	NAME	FUNCTION			
13	SUPP	Positive Charge-Pump Driver Supply Voltage. Bypass to PGND with a $0.1\mu$ F capacitor.			
14	PGND	Power Ground. Connect to GND underneath the IC.			
15	LX	Main Boost Regulator Power MOSFET N-Channel Drain. Connect output diode and output capacitor as close to PGND as possible.			
16	TGND	Must be connected to ground.			

## **Detailed Description**

The MAX1748 is a highly efficient triple-output power supply for TFT LCD applications. The device contains one high-power step-up converter and two low-power charge pumps. The primary boost converter uses an internal N-channel MOSFET to provide maximum efficiency and to minimize the number of external components. The output voltage of the main boost converter (VMAIN) can be set from VIN to 13V with external resistors.

The dual charge pumps independently regulate a positive output (VPOS) and a negative output (VNEG). These low-power outputs use external diode and capacitor stages (as many stages as required) to regulate output voltages up to +40V and down to -40V. A proprietary regulation algorithm minimizes output ripple as well as capacitor sizes for both charge pumps.

Also included in the MAX1748 are a precision 1.25V reference that sources up to 50µA, logic shutdown, soft-start, power-up sequencing, fault detection, and an active-low open-drain ready output.

### Main Boost Converter

The MAX1748 main step-up converter switches at a constant 1MHz internal oscillator frequency to allow the use of small inductors and output capacitors. The MOSFET switch pulse width is modulated to control the power transferred on each switching cycle and to regulate the output voltage.

During PWM operation, the internal clock's rising edge sets a flip-flop, which turns on the N-channel MOSFET (Figure 1). The switch turns off when the sum of the voltage-error, slope-compensation, and current-feedback signals trips the multi-input comparator and resets the flip-flop. The switch remains off for the rest of the clock cycle. Changes in the output voltage error signal shift the switch current trip level, consequently modulating the MOSFET duty cycle.

## **Dual Charge-Pump Regulator**

The MAX1748 contains two individual low-power charge pumps. One charge pump inverts the supply voltage (SUPN) and provides a regulated negative output voltage. The second charge pump doubles the supply voltage (SUPP) and provides a regulated positive output voltage. The MAX1748 contains internal P-channel and N-channel MOSFETs to control the power transfer. The internal MOSFETs switch at a constant 500kHz ( $0.5 \times f_{OSC}$ ).

### Negative Charge Pump

During the first half-cycle, the P-channel MOSFET turns on and the flying capacitor C5 charges to V<sub>SUPN</sub> minus a diode drop (Figure 2). During the second half-cycle, the P-channel MOSFET turns off, and the N-channel MOSFET turns on, level shifting C5. This connects C5 in parallel with the reservoir capacitor C6. If the voltage across C6 minus a diode drop is lower than the voltage across C5, charge flows from C5 to C6 until the diode (D5) turns off. The amount of charge transferred to the output is controlled by the variable N-channel on-resistance.

### Positive Charge Pump

During the first half-cycle, the N-channel MOSFET turns on and charges the flying capacitor C3 (Figure 3). This initial charge is controlled by the variable N-channel on-resistance. During the second half-cycle, the Nchannel MOSFET turns off and the P-channel MOSFET turns on, level shifting C3 by V<sub>SUPP</sub> volts. This connects C3 in parallel with the reservoir capacitor C4. If the voltage across C4 plus a diode drop (V<sub>POS</sub> + V<sub>DIODE</sub>) is smaller than the level-shifted flying capacitor voltage (V<sub>C3</sub> + V<sub>SUPP</sub>), charge flows from C3 to C4 until the diode (D3) turns off.

### Soft-Start

For the main boost regulator, soft-start allows a gradual increase of the internal current-limit level during startup to reduce input surge currents. The MAX1748 divides





Figure 1. PWM Boost Converter Block Diagram

## Shutdown

**MAX1748** 

the soft-start period into four phases. During phase 1, the MAX1748 limits the current limit to only 0.38A (see *Electrical Characteristics*), approximately a quarter of the maximum current limit ( $I_{LX(MAX)}$ ). If the output does not reach regulation within 1ms, soft-start enters phase II and the current limit is increased by another 25%. This process is repeated for phase III. The maximum 1.5A (typ) current limit is reached within 3.0ms or when the output reaches regulation, whichever occurs first (see the Startup Waveforms in the *Typical Operating Characteristics*).

For the charge pumps, soft-start is achieved by controlling the rise rate of the output voltage. The output voltage regulates within 4ms, regardless of output capacitance and load, limited only by the regulator's output impedance. A logic-low level on SHDN disables all three MAX1748 converters and the reference. When shut down, supply current drops to 0.1µA to maximize battery life and the reference is pulled to ground. The output capacitance and load current determine the rate at which each output voltage will decay. A logic-level high on SHDN power activates the MAX1748 (see *Power-Up Sequencing*). Do not leave SHDN floating. If unused, connect SHDN to IN.

## **Power-Up Sequencing**

Upon power-up or exiting shutdown, the MAX1748 starts a power-up sequence. First, the reference powers up. Then the main DC-DC step-up converter powers up with soft-start enabled. Once the main boost





Figure 2. Negative Charge-Pump Block Diagram



Figure 3. Positive Charge-Pump Block Diagram

converter reaches regulation, the negative charge pump turns on. When the negative output voltage reaches approximately 88% of its nominal value (VFBN < 110mV), the positive charge pump starts up. Finally, when the positive output voltage reaches 90% of its nominal value (VFBP > 1.125V), the active-low ready signal ( $\overline{\text{RDY}}$ ) goes low (see *Power Ready* section).

#### **Power Ready**

Power ready is an open-drain output. When the powerup sequence is properly completed, the MOSFET turns on and pulls RDY low with a typical 125 $\Omega$  on-resistance. If a fault is detected, the internal open-drain MOSFET appears as a high impedance. Connect a 100k $\Omega$  pull-up resistor between RDY and IN for a logiclevel output.

#### **Fault Detection**

Once RDY is low and if any output falls below its faultdetection threshold, RDY goes high impedance.

For the reference, the fault threshold is 1.05V. For the main boost converter, the fault threshold is 88% of its nominal value (V<sub>FB</sub> < 1.1V). For the negative charge pump, the fault threshold is approximately 90% of its nominal value (V<sub>FBN</sub> < 130mV). For the positive charge pump, the fault threshold is 88% of its nominal value (V<sub>FBP</sub> < 1.11V).

Once an output faults, all outputs later in the power sequence shut down until the faulted output rises above its power-up threshold. For example, if the negative charge-pump output voltage falls below the fault detection threshold, the main boost converter remains active while the positive charge pump stops switching and its output voltage decays, depending on output capacitance and load. The positive charge-pump output will not power up until the negative charge-pump output voltage rises above its power-up threshold (see the *Power-Up Sequencing* section).

#### Voltage Reference

The voltage at REF is nominally 1.25V. The reference can source up to 50µA with good load regulation (see *Typical Operating Characteristics*). Connect a 0.22µF bypass capacitor between REF and GND.

### Design Procedure

#### **Main Boost Converter**

#### **Output Voltage Selection**

Adjust the output voltage by connecting a voltage divider from the output (V<sub>MAIN</sub>) to FB to GND (see *Typical Operating Circuit*). Select R2 in the 10k $\Omega$  to 20k $\Omega$  range. Higher resistor values improve efficiency at low output current but increase output voltage error



due to the feedback input bias current. Calculate R1 with the following equations:

### $R1 = R2 [(V_{MAIN} / V_{REF}) - 1]$

where  $V_{REF} = 1.25V$ .  $V_{MAIN}$  may range from  $V_{IN}$  to 13V.

#### Feedback Compensation

For stability, add a pole-zero pair from FB to GND in the form of a series resistor (R<sub>COMP</sub>) and capacitor (C<sub>COMP</sub>). The resistor should be half the value of the R2 feedback resistor.

#### Inductor Selection

Inductor selection depends on input voltage, output voltage, maximum current, switching frequency, size, and availability of inductor values. Other factors can include efficiency and ripple voltage. Inductors are specified by their inductance (L), peak current (IPEAK), and resistance (RL). The following boost-circuit equations are useful in choosing inductor values based on the application. They allow the trading of peak current and inductor value while allowing for consideration of component availability and cost.

The following equation includes a constant LIR, which is the ratio of the inductor peak-to-peak AC current to maximum average DC inductor current. A good compromise between the size of the inductor, loss, and output ripple is to choose an LIR of 0.3 to 0.5. The peak inductor current is then given by:

$$I_{PEAK} = \frac{I_{MAIN(MAX)} \times V_{MAIN}}{Efficiency \times V_{IN(MIN)}} \times [1 + (LIR/2)]$$

The inductance value is then given by:

$$L = \frac{V_{IN(MIN)}^{2} \times \text{Efficiency} \times (V_{MAIN} - V_{IN(MIN)})}{V_{(MAIN)}^{2} \times \text{LIR} \times I_{MAIN(MAX)} \times f_{OSC}}$$

Considering the typical application circuit, the maximum DC load current (IMAIN(MAX)) is 200mA with a 10V output. A 6.8µH inductance value is then chosen, based on the above equations and using 85% efficiency and a 1MHz operating frequency. Smaller inductance values typically offer a smaller physical size for a given series resistance and current rating, allowing the smallest overall circuit dimensions. However, due to higher peak inductor currents, the output voltage ripple (IPEAK × output filter capacitor ESR) will be higher.

Use inductors with a ferrite core or equivalent; powder iron cores are not recommended for use with the MAX1748's high switching frequencies. The inductor's maximum current rating should exceed IPEAK. Under fault conditions, inductor current may reach up to 2.0A.

The inductor's DC resistance significantly affects efficiency. For best performance, select inductors with resistance less than the internal N-channel FET resistance. To minimize radiated noise in sensitive applications, use a shielded inductor.

The inductor should have as low a series resistance as possible. For continuous inductor current, the power loss in the inductor resistance, PLR, is approximated by:

 $P_{LR} \cong (I_{MAIN} \times V_{MAIN} / V_{IN})^2 \times R_L$ 

where RL is the inductor series resistance.

### **Output Capacitor**

A 10µF capacitor works well in most applications. The equivalent series resistance (ESR) of the output filter capacitor affects efficiency and output ripple. Output voltage ripple is largely the product of the peak inductor current and the output capacitor ESR. Use low-ESR ceramic capacitors for best performance. Low-ESR, surface-mount tantalum capacitors with higher capacity may be used for load transients with high peak currents. Voltage ratings and temperature characteristics should be considered.

### Input Capacitor

The input capacitor (C<sub>IN</sub>) in boost designs reduces the current peaks drawn from the input supply and reduces noise injection. The value of C<sub>IN</sub> is largely determined by the source impedance of the input supply. High source impedance requires high input capacitance, particularly as the input voltage falls. Since step-up DC-DC converters act as "constant-power" loads to their input supply, input current rises as input voltage falls. A good starting point is to use the same capacitance value for C<sub>IN</sub> as for C<sub>OUT</sub>. Table 1 lists suggested component suppliers.

### Integrator Capacitor

The MAX1748 contains an internal current integrator that improves the DC load regulation but increases the peak-to-peak transient voltage (see the load-transient waveforms in the *Typical Operating Characteristics*). For highly accurate DC load regulation, enable the current integrator by connecting a 470pF capacitor to INTG. To minimize the peak-to-peak transient voltage at the expense of DC regulation, disable the integrator by connecting INTG to REF and adding a 100k $\Omega$  resistor to GND.

Use a Schottky diode with an average current rating equal to or greater than the peak inductor current, and a voltage rating at least 1.5 times the main output voltage (V<sub>MAIN</sub>).

## Charge Pump

### Efficiency Considerations

The efficiency characteristics of the MAX1748 regulated charge pumps are similar to a linear regulator. They are dominated by quiescent current at low output currents and by the input voltage at higher output currents (see *Typical Operating Characteristics*). So the maximum efficiency may be approximated by:

Efficiency  $\cong$  V<sub>NEG</sub> / [V<sub>IN</sub> × N]; for the negative charge pump

Efficiency  $\cong$  VPOS / [VIN × (N + 1)]; for the positive charge pump

where N is the number of charge-pump stages.

### **Output Voltage Selection**

Adjust the positive output voltage by connecting a voltage-divider from the output (VPOS) to FBP to GND (see *Typical Operating Circuit*). Adjust the negative output

## Table 1. Component Suppliers

SUPPLIER	PHONE	FAX					
INDUCTORS							
Coilcraft	847-639-6400	847-639-1469					
Coiltronics	561-241-7876	561-241-9339					
Sumida USA	847-956-0666	847-956-0702					
Toko	847-297-0070	847-699-1194					
CAPACITORS							
AVX	803-946-0690	803-626-3123					
Kemet	408-986-0424	408-986-1442					
Sanyo	619-661-6835	619-661-1055					
Taiyo Yuden	408-573-4150	408-573-4159					
DIODES							
Central Semiconductor	516-435-1110	516-435-1824					
International Rectifier	310-322-3331	310-322-3332					
Motorola	602-303-5454	602-994-6430					
Nihon	847-843-7500	847-843-2798					
Zetex	516-543-7100	516-864-7630					

voltage by connecting a voltage-divider from the output (V<sub>NEG</sub>) to FBN to REF. Select R4 and R6 in the 50k $\Omega$  to 100k $\Omega$  range. Higher resistor values improve efficiency at low output current but increase output voltage error due to the feedback input bias current. Calculate the remaining resistors with the following equations:

$$R3 = R4 \left[ (V_{POS} / V_{REF}) - 1 \right]$$

$$R5 = R6 (V_{NEG} / V_{REF})$$

where  $V_{REF} = 1.25V$ . VPOS may range from VSUPP to 40V, and VNEG may range from 0 to -40V.

#### Flying Capacitor

Increasing the flying capacitor's value reduces the output current capability. Above a certain point, increasing the capacitance has a negligible effect because the output current capability becomes dominated by the internal switch resistance and the diode impedance. Start with  $0.1\mu F$  ceramic capacitors. Smaller values may be used for low-current applications.

### Charge-Pump Output Capacitor

Increasing the output capacitance or decreasing the ESR reduces the output ripple voltage and the peak-topeak transient voltage. Use the following equation to approximate the required capacitor value:

 $COUT \ge [IOUT / (500 kHz \times VRIPPLE)]$ 

#### Charge-Pump Input Capacitor

Use a bypass capacitor with a value equal to or greater than the flying capacitor. Place the capacitor as close to the IC as possible. Connect directly to PGND.

#### **Rectifier Diode**

Use Schottky diodes with a current rating equal to or greater than 4 times the average output current, and a voltage rating at least 1.5 times V<sub>SUPP</sub> for the positive charge pump and V<sub>SUPN</sub> for the negative charge pump.

## PC Board Layout and Grounding

Careful printed circuit layout is extremely important to minimize ground bounce and noise. First, place the main boost converter output diode and output capacitor less than 0.2in (5mm) from the LX and PGND pins with wide traces and no vias. Then place 0.1µF ceramic bypass capacitors near the charge-pump input pins (SUPP and SUPN) to the PGND pin. Keep the chargepump circuitry as close to the IC as possible, using wide traces and avoiding vias when possible. Locate all feedback resistive dividers as close to their respective feedback pins as possible. The PC board should feature separate GND and PGND areas connected at only one point under the IC. To maximize output power and efficiency and to minimize output power ripple voltage, use extra wide power ground traces and solder the IC's power ground pin directly to it. Avoid having sensitive traces near the switching nodes and high-current lines.

Refer to the MAX1748 evaluation kit for an example of proper board layout.

## Applications Information

### Boost Converter Using a Cascoded MOSFET

For applications that require output voltages greater than 13V, cascode an external N-channel MOSFET (Figure 4). Place the MOSFET as close to the LX pin as possible. Connect the gate to the input voltage ( $V_{IN}$ ) and the source to LX.

### **MOSFET Selection**

Choose a MOSFET with an on-resistance (R<sub>DS(ON)</sub>) lower than the internal N-channel MOSFET. Lower R<sub>DS(ON)</sub> will improve efficiency. The external N-channel MOSFET must have a drain-voltage rating higher than the main output voltage (V<sub>MAIN</sub>).

## Chip Information

TRANSISTOR COUNT: 2846



Figure 4. Power Supply Using Cascoded MOSFET



**MAX1748** 





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